



D₂

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON) max}	I _D T _A = +25°C
-30V	$48m\Omega @ V_{GS} = -10V$	-4.8A
	$57mΩ @ V_{GS} = -4.5V$	-4.4A
	$80m\Omega @ V_{GS} = -2.5V$	-3.7A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

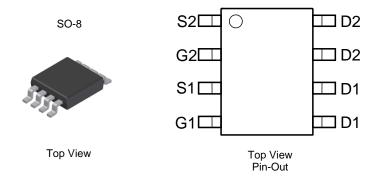
- DC-DC Converters
- Power Management Functions
- Backlighting

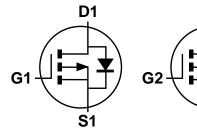
Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.074 grams (Approximate)





Equivalent Circuit

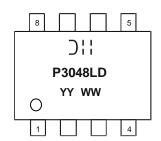
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3048LSD-13	SO-8	2500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



);; = Manufacturer's Marking
P3048LD = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	-30	V		
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 6) $V_{GS} = -10V$ Steady $T_A = +25^{\circ}C$ state $T_A = +70^{\circ}C$				-4.8 -3.8	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	-35	Α		
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-3.5	Α
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	-19	Α
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	19	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	Б	102	°C/W
Themal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ hetaJA}$	57	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	Б	75	°C/W
Themal Resistance, Junction to Ambient (Note o)	t<10s	$R_{ hetaJA}$	40	
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	18	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

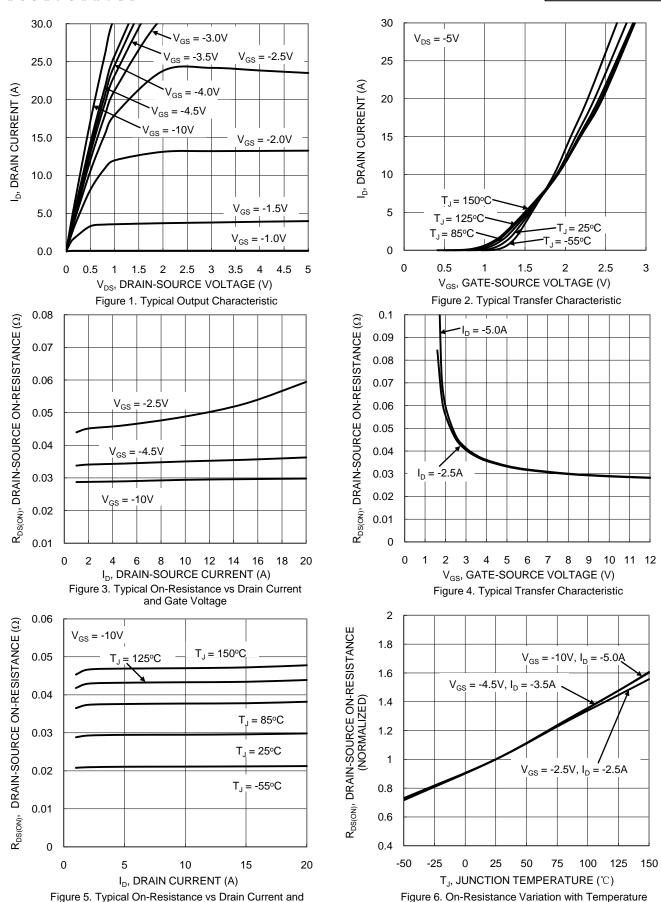
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1.0	μΑ	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5		-1.3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
		_	28	48		$V_{GS} = -10V, I_D = -5A$
Static Drain-Source On-Resistance	R _{DS(ON)}	-	34	57	$m\Omega$	$V_{GS} = -4.5V$, $I_D = -3.5A$
		_	44	80		$V_{GS} = -2.5V, I_D = -2.5A$
Diode Forward Voltage	V_{SD}	_	-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	_	1438	_	pF	15)/)/ 0)/
Output Capacitance	Coss	_	92	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ -f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	76	_	pF	1 = 1.0IVII IZ
Gate Resistance	R_g	_	11.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -10V)	Qg	_	29.6	_	nC	
Total Gate Charge (V _{GS} = -4.5V)	Qq	_	13.5	_	nC	$V_{DS} = -20V$,
Gate-Source Charge	Q _{gs}	_	2.4	_	nC	$I_D = -5A$
Gate-Drain Charge	Q _{gd}	_	3.0	_	nC	
Turn-On Delay Time	t _{D(ON)}	_	2.5	_	ns	
Turn-On Rise Time	t _R	_	2.7	_	ns	$V_{DS} = -15V, V_{GS} = -10V,$
Turn-Off Delay Time	t _{D(OFF)}		108	_	ns	$R_L = 3\Omega$, $R_G = 6\Omega$
Turn-Off Fall Time	t _F	_	34	_	ns	1
Reverse Recovery Time	t _{RR}		10	_	ns	$I_F = -5.0A$, $di/dt = 100A/\mu s$
Reverse Recovery Charge	Q_{RR}	_	3.6	_	nC	I _F = -5.0A, di/dt = 100A/μs

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. Notes:

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





Temperature



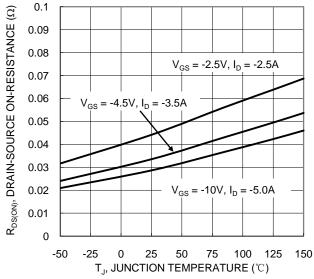


Figure 7. On-Resistance Variation with Temperature

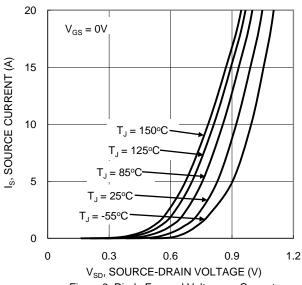


Figure 9. Diode Forward Voltage vs Current 10 8 6 $V_{GS}(V)$ 4 $V_{DS} = -20V, I_{D} = -5A$ 2 0 0 5 10 20 25 30 15 Q_g (nC) Figure 11. Gate Charge

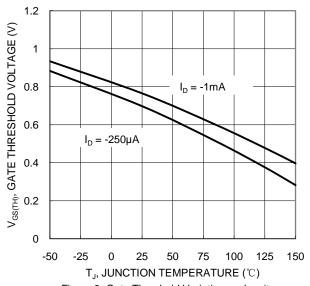
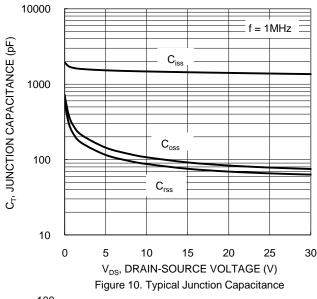
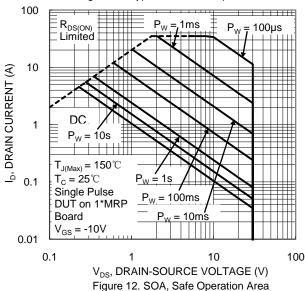


Figure 8. Gate Threshold Variation vs Junciton Temperature







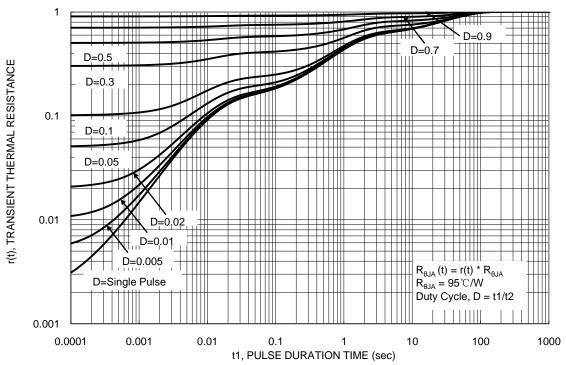


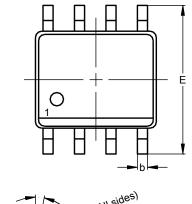
Figure 13. Transient Thermal Resistance

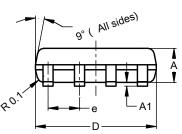


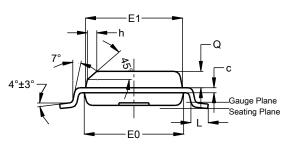
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8





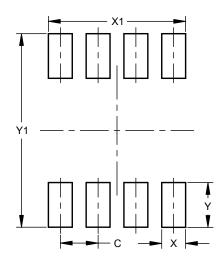


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h	-		0.35		
L	0.62	0.82	0.72		
Ø	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)			
С	1.27			
Х	0.802			
X1	4.612			
Y	1.505			
Y1	6.50			



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